

Title (en)

A HIGH ELECTRON MOBILITY FIELD EFFECT TRANSISTOR AND METHOD OF MANUFACTURING THE SAME

Title (de)

FELDEFFEKTTRANSISTOR MIT HOHER ELEKTRONENMOBILITÄT UND VERFAHREN ZUR HERSTELLUNG DAVON

Title (fr)

TRANSISTOR À EFFET DE CHAMP À HAUTE MOBILITÉ ÉLECTRONIQUE ET PROCÉDÉ DE FABRICATION ASSOCIÉ

Publication

**EP 2852979 A1 20150401 (EN)**

Application

**EP 13793952 A 20130509**

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- US 201213478609 A 20120523
- US 201213479018 A 20120523
- US 2013040441 W 20130509

Abstract (en)

[origin: WO2013176905A1] A high electron mobility field effect transistor (HEMT) includes a two dimensional electron gas (2DEG) in the drift region between the gate and the drain that has a non-uniform lateral 2DEG distribution that increases in a direction in the drift region from the gate to the drain.

IPC 8 full level

**H01L 29/778** (2006.01); **H01L 21/336** (2006.01); **H01L 29/34** (2006.01); **H01L 21/311** (2006.01); **H01L 29/20** (2006.01); **H01L 29/423** (2006.01)

CPC (source: EP)

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BA ME

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